Product data sheet

1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- · Reverse battery protection
- Power management
- High-side loadswitch
- Motor drive

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|--|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | -60 | V | |
| V_{GS} | gate-source voltage | | [1] | -20 | - | 20 | V | |
| I _D | drain current | V _{GS} = -10 V; T _{mb} = 25 °C | | - | - | -25 | Α | |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | | - | - | 66 | W | |
| Static charac | Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -10 V; I_D = -4.7 A; T_j = 25 °C | | - | 48 | 61 | mΩ | |

[1] $V_{GS} = -20 \text{ V/+}5 \text{ V}$ according AEC-Q101 at $T_i = 175 \text{ °C}$; $V_{GS} = -20 \text{ V/+}20 \text{ V}$ according AEC-Q101 at $T_i = 150 \text{ °C}$



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---------------------------------|----------------|
| 1 | S | source | mb | D |
| 2 | S | source | | |
| 3 | S | source | | G (FY) |
| 4 | G | gate | | s |
| mb | D | mounting base; connected to drain | LFPAK56; Power- SO8 (SOT669) | 017aaa094 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|-----------------------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| BUK6Y61-60P | LFPAK56; Power-SO8 | plastic, single-ended surface-mounted package; 4 terminals | SOT669 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK6Y61-60P | 6Y6160P |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----|-----|-------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -60 | V |
| V _{GS} | gate-source voltage | | [1] | -20 | 20 | V |
| I _D | drain current | V _{GS} = -10 V; T _{mb} = 25 °C | | - | -25 | Α |
| | | V _{GS} = -10 V; T _{mb} = 100 °C | | - | -17.7 | Α |
| I _{DM} | peak drain current | single pulse; t _p ≤ 10 µs; T _{mb} = 25 °C | | - | -100 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | | - | 66 | W |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |
| Source-drain | n diode | | | | | |
| Is | source current | T _{mb} = 25 °C | | - | -25 | Α |
| I _{SM} | peak source current | single pulse; t _p ≤ 10 µs; T _{mb} = 25 °C | | - | -100 | Α |
| ESD maximu | um rating | | | - | ' | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [2] | - | 800 | V |
| Avalanche r | uggedness | | ' | 1 | | - |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = -4.6 A; DUT in valanche (unclamped) | | - | 61 | mJ |

- [1] $V_{GS} = -20 \text{ V/+5 V}$ according AEC-Q101 at $T_j = 175 \text{ °C}$; $V_{GS} = -20 \text{ V/+20 V}$ according AEC-Q101 at $T_j = 150 \text{ °C}$
- [2] Measured between all pins.

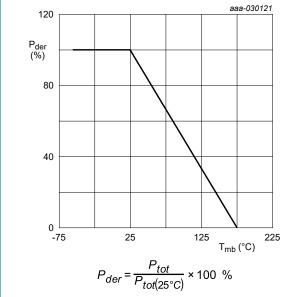
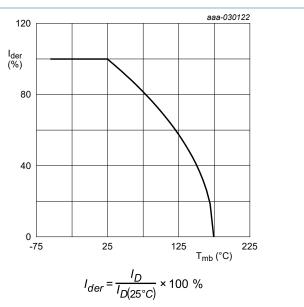


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



ig. 2. Normalized continuous drain current as a function of mounting base temperature

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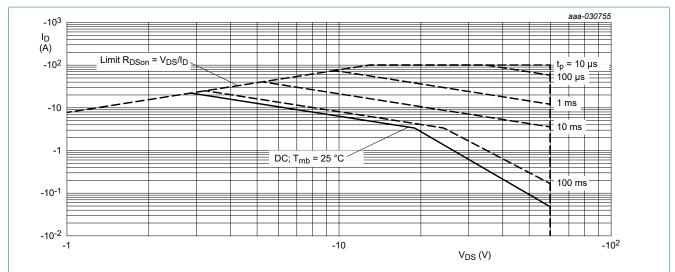
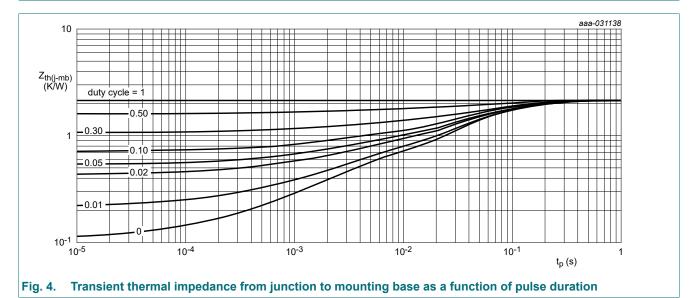


Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | | - | 1.8 | 2.3 | K/W |



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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|--|------|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C | -60 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | -1.5 | -2 | -3 | V |
| I _{DSS} | drain leakage current | V _{DS} = -60 V; V _{GS} = 0 V; T _j = 25 °C | - | - | -1 | μΑ |
| | | V _{DS} = -60 V; V _{GS} = 0 V; T _j = 125 °C | - | - | -10 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| | | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = -10 V; I_D = -4.7 A; T_j = 25 °C | - | 48 | 61 | mΩ |
| r | resistance | V _{GS} = -10 V; I _D = -4.7 A; T _j = 175 °C | - | 100 | 130 | mΩ |
| | | V_{GS} = -4.5 V; I_D = -3.8 A; T_j = 25 °C | - | 62 | 93 | mΩ |
| 9 _{fs} | forward transconductance | $V_{DS} = -10 \text{ V}; I_D = -4 \text{ A}; T_j = 25 \text{ °C}$ | - | 65 | - | S |
| R_G | gate resistance | f = 1 MHz; T _j = 25 °C | - | 12 | - | Ω |
| Dynamic ch | aracteristics | | ' | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = -30 V; I _D = -4.7 A; V _{GS} = -10 V; | - | 20 | 30 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 3.3 | - | nC |
| Q_{GD} | gate-drain charge | | - | 4.3 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -30 V; f = 1 MHz; V _{GS} = 0 V; | - | 1060 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 85 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 49 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = -30 V; I _D = -4.7 A; V _{GS} = -10 V; | - | 12 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 58 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 21 | - | ns |
| t _f | fall time | | - | 204 | - | ns |
| Source-drai | in diode | | | | | |
| V_{SD} | source-drain voltage | I _S = -22.4 A; V _{GS} = 0 V; T _j = 25 °C | - | -0.7 | -1.2 | V |
| t _{rr} | reverse recovery time | I _S = -22.4 A; dI _S /dt = 100 A/µs; | - | 30 | - | ns |
| Q _r | recovered charge | $V_{GS} = -10 \text{ V}; V_{DS} = -30 \text{ V}; T_j = 25 \text{ °C}$ | - | 37 | - | nC |

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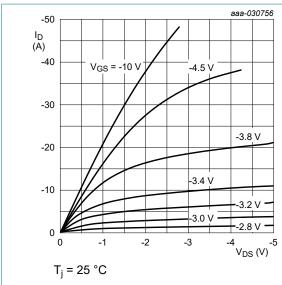


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

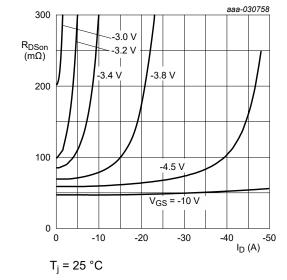


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

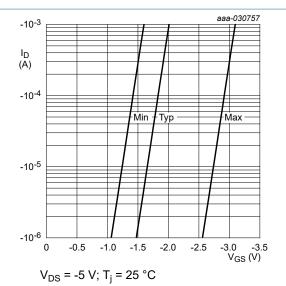


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

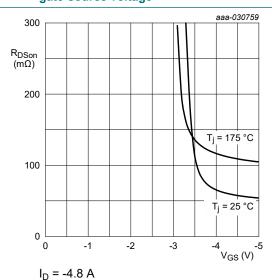


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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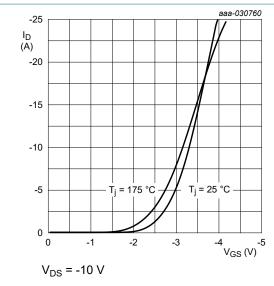


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

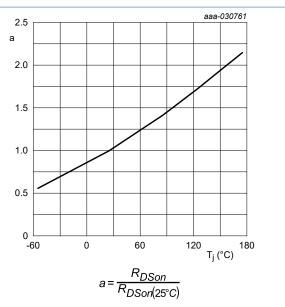


Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values

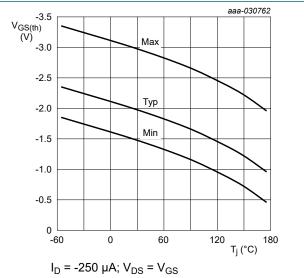


Fig. 11. Gate-source threshold voltage as a function of junction temperature

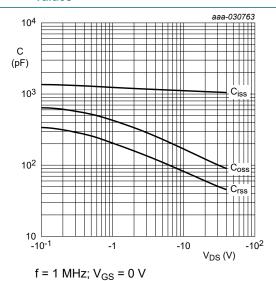


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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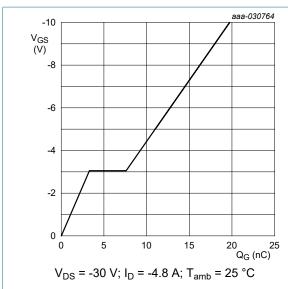


Fig. 13. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

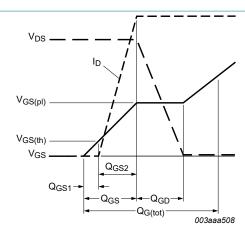


Fig. 14. Gate charge waveform definitions

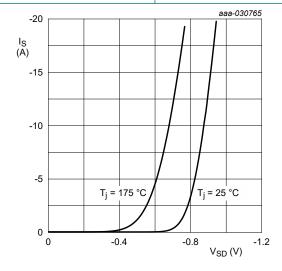
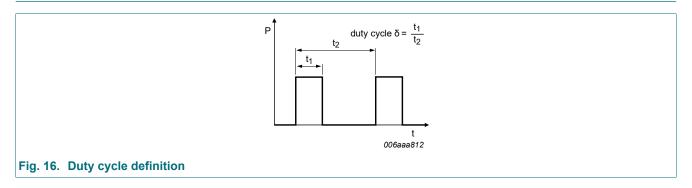


Fig. 15. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

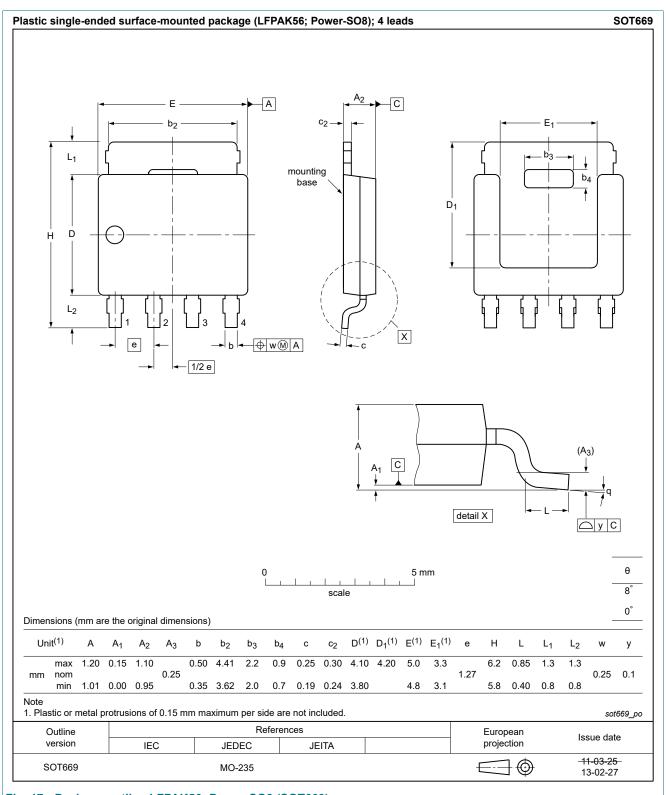


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| BUK6Y61-60P v.1 | 20200316 | Product data sheet | - | - |

60 V, P-channel Trench MOSFET

14. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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